

ABSTRACT

There is provided a semiconductor device capable of improving the performance and reliability of a device. The semiconductor device comprising an active pattern including, a lower pattern extending in a first direction, and a plurality of sheet patterns spaced apart from the lower pattern in a second direction perpendicular to the first direction, wherein the lower pattern includes a semiconductor material, a plurality of gate structures on the lower pattern and spaced apart from each other in the first direction, wherein each of the plurality of gate structures includes a gate electrode and a gate insulating film, a source/drain recess between adjacent ones of the gate structures, wherein a bottom of the source/drain recess is in the lower pattern, a bottom insulating liner in the bottom of the source/drain recess, and a source/drain pattern in the source/drain recess and on top of the bottom insulating liner.

FIG. 2